1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-30812GVA

2. Structure :

2-1. Planar type : P/N Diode
2-2. Electrodes :
Top side : Gold pad.
Back side : SnAu alloy.

3. Size :

3-1. ※1Chip size : 8.5 mils x 8.5 mils (0.215 mm x 0.215 mm).
3-2. Chip thickness : 4.0 ± 1.0 mils (0.100 ± 0.025 mm)
3-3. Active area : 5.3 mils x 5.3 mils (0.135 mm x 0.135 mm).
3-4. ※2Bonding pad : 5.9 mils x 5.9 mils (0.150 mm x 0.150 mm) .
3-5. Pattern drawing : Refer to the attached drawing.

※1Including scribing line. The chip size is about $(0.190\pm0.015)^2$mm^2 after dicing.
※2 The bonding pad dimension is $(0.150\pm0.005)^2$mm^2 after etching.

4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	V_R=9V Ee=0mW/cm^2			100	nA
Zener Voltage	Vz	I_Z=5mA Ee=0mW/cm^2	10		14	V
Forward Voltage	Vf	I_F=20mA Ee=0mW/cm^2	0.75		1.2	V